On the "bendable" ALPIDE-inspired MAPS in 65 nm technology

Magnus Mager (CERN) on behalf of the ALICE collaboration The 2021 international workshop on the high energy Circular Electron-Positron Collider (CEPC 2021) 8 Nov 2021







Overview



Background

- material budget breakdown of detectors (ALICE ITS2)
- thin monolithic sensors
- proposal for ALICE ITS3

R&D highlights

- bending silicon
- first prototypes in 65 nm technology

Outlook

towards the wafer-scale sensor





ALICE LS2 upgrades with Monolithic Active Pixel Sensors (MAPS)





Inner Tracking System

LS2

6 layers:

2 hybrid silicon pixel

- 2 silicon drift
- 2 silicon strip

Inner-most layer:

radial distance: 39 mm material: $X/X_0 = 1.14\%$ pitch: $50 \times 425 \ \mu m^2$ rate capability: 1 kHz

7 layers: all MAPS 10 m², 24k chips, 12.5 Giga-Pixels

Inner-most layer:

radial distance: 23 mm material: $X/X_0 = 0.35\%$ pitch: $29 \times 27 \ \mu m^2$ rate capability: 100 kHz (Pb-Pb)

Muon Forward Tracker

new detector

5 discs, double sided: based on same technology as ITS2













Inner Barrel (IB) Flexible PCB 3 Inner Layers: 12+16+20 Staves 9 sensors **1** Module / Stave **Cold Plate 9** sensors per Module Space Frame 96 Modules to be produced (including one spare barrel) **Outer Barrel (OB)** Power Bus Flexible PCB 2 Middle Layers: 30+24 Staves 2×4 Modules / Stave 2 x 7 sensors 2 Outer Layers: 42+48 Staves 2×7 Modules / Stave 2×7 sensors / Module Half-Stave Half-Stave (Middle and Outer Layers are equipped with the same Module

1880 Modules to be produced (including spares)











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PIXEL PERFECT

A CERN for climate change



ITS2 inner barrel



- ITS2 is expected to perform according to specifications or even better
- The Inner Barrel is ultra-light but rather packed \rightarrow further improvements seem possible
- Key questions: Can we get closer to the IP? Can we reduce the material further?



ITS2: assembled three inner-most half-layers



Material budget a closer look



- Observations:
 - Si makes only **1/7th** of total material
 - irregularities due to support/cooling
- Removal of water cooling
 - **possible** if power consumption stays below 20 mW/cm²





- Removal of the circuit board (power+data) **possible** if integrated on chip
- Removal of mechanical support
 - **benefit** from increased stiffness by rolling Si wafers



ITS3 performance figures

pointing resolution



[ALICE-PUBLIC-2018-013]

improvement of factor 2 over all momenta



tracking efficiency



large improvement for low transverse momenta



Monolithic Active Pixel Sensor Idea (1): make use of the flexible nature of thin silicon







Silicon Genesis: 20 micron thick wafer









Detector modules Idea (2): build wafer-scale sensors



- Chip size is traditionally limited by CMOS manufacturing ("reticle size")
 - typical sizes of few cm²
 - modules are tiled with chips connected to a flexible printed circuit board

- New option: stitching, i.e. aligned exposures of a reticle to produce larger circuits
 - actively used in industry
 - a 300 mm wafer can house a sensor to equip a full half-layer





- requires dedicated sensor design





R&D (1): bending S





["Standard", 50 µm thick ALPIDEs as used for the ITS2 IB, are already quite flexible!]





Bending ALPIDE exampl

tension wire

1100

50 µm-thick ALPIDE

out out out out out

foi

R = 18 mm jig



Beam tests 1st paper: <u>arxiv:2105.13000</u>



Fig. 10: Inefficiency as a function of threshold for different rows and incident angles with partially logarithmic scale (10^{-1} to 10^{-5}) to show fully efficient rows. Each data point corresponds to at least 8k tracks.



	- 511	0.0°
	- 447	- 4.9°
•	- 383	- 9.7°
	- 319	- 14.6° <u>එ</u>
	- 255 og	- 19.5° ter
	191	- 24.4° <u>-</u>
	- 127	- 29.2°
	- 63	-34.1°
00	0	39.0°



First demonstration of in-beam performance of bent Monolithic Active Pixel Sensors

ALICE ITS3

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Abstract

A novel approach for designing the next generation of vertex detectors foresees to employ wafer-scale sensors that can be bent to truly cylindrical geometries after thinning them to thicknesses of 20-40 µm. To solidify this concept. the feasibility of operating bent MAPS was demonstrated using $1.5 \text{ cm} \times 3 \text{ cm}$ ALPIDE chips. Already with their thickness of 50 µm, they can be successfully bent to radii of about 2 cm without any signs of mechanical or electrical damage. During a subsequent characterisation using a 5.4 GeV electron beam, it was further confirmed that they preserve their full electrical functionality as well as particle detection performance.

In this article, the bending procedure and the setup used for characterisation are detailed. Furthermore, the analysis of the beam test, including the measurement of the detection efficiency as a function of beam position and local inclination angle, is discussed. The results show that the sensors maintain their excellent performance after bending to radii of $2 \,\mathrm{cm}$, with detection efficiencies above 99.9% at typical operating conditions, paving the way towards a new class of detectors with unprecedented low material budget and ideal geometrical properties.

Keywords: Monolithic Active Pixel Sensors, Solid state detectors, Bent sensors

1 1. Introduction

The precision of barrel vertex detectors is mainly determined by three con-

• tributions: their radial distance to the interaction point, their material budget.

a and their intrinsic sensor resolution. In order to achieve hermiticity, they are

typically built out of detector staves placed in layers around the beam pipe. This

arrangement effectively sets a practical limit on the first two factors. ALICE,

*Corresponding author

Proprint submitted to Nucl. Instrum. Methods Phys. Res. A

February 22, 2021

Clearly proving that bent MAPS are working!



Beam tests µITS3

- µITS3, i.e. 6 ALPIDEs at ITS3 radii
 - two complete setups based on "gold" quality **ALPIDE** chips
 - one has a Cu target in the center: expect to see 120 GeV proton/pion–Cu collisions
- Several days of continuous data taking
 - detailed analysis ongoing







First "real" experiment, allows to study tracking/reconstruction



Beam tests µITS3





First "real" experiment, allows to study tracking/reconstruction





Bending of wafer-scale sensors procedure



30 mm (L2) 50 µm dummy Silicon



Layer assembly



3-layer integration successful!



R&D (2): MAPS in 65 nm



65 nm prototypes, MLR1





First submission in TowerJazz 65nm

- scoped within CERN EP R&D WP1.2
- significant drive from ITS3
- + important contributions from outside (not ALICE) groups
- Contained several test chips
 - radiation test structures
 - pixel test structures
 - pixel matrices
 - analog building blocks (band gaps, LVDS drivers, etc)

Very versatile first submission, combining what was initially planned for 2 MPWs



65 nm prototypes, MLR1

~12 mm



16 mm



- Fully processed wafers are back by now
 - testing has started at many places
- Produced with 4 different process splits
 - TCAD-guided optimisations in collaboration with foundry, comparable to TJ180nm





65 nm prototypes, MLR1 **Digital Pixel Test Structure (DPTS)**

- Most "aggressive" chip in MLR1
- > 32×32 pixels, 15 µm pitch
 - sizeable prototype, allows for "easy" test beam integration
- Asynchronous digital readout with ToT information
- Allows to verify:
 - sensor performance
 - front-end performance
 - basic digital building blocks
 - SEU cross-sections of registers







First beam test Telescope with DPTS

- Scintillator with 1mm hole can be used to trigger on narrow beam spot
- 6 precision linear stages with remote control allow to precisely align 2 DTPS and scintillators





scintilator

XY-stage

scintilator

3 ALPIDE 2 DPTS 3 ALPIDE

XY-stage









first few % of total statistics analysed





Beam spot and trigger tuned to illuminate a small area





first few % of total statistics analysed





wafer: 22 version: 1 split: 4 (opt.)

- $V_{pwell} = -1.2 V$ $V_{sub} = -1.2 V$ $I_{reset} = 10 \, \text{pA}$ $I_{bias} = 100 \text{ nA}$ $I_{biasn} = 10 \, \mathrm{nA}$ $I_{db} = 100 \, \text{nA}$ $V_{casn} = 300 \,\mathrm{mV}$ $V_{casb} = 250 \,\mathrm{mV}$
- Beam spot and trigger tuned to illuminate a small area
- Looking at tracks without hit in the DPTS, a clear 100% shadow is seen







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- The area matches precisely the DPTS
- 166/166 tracks in region of interest





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 - and even for both in coincidence (83/83)









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Excellent sensor and front-end performance already from first 65 nm prototype





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Beam spot illuminate a	Beam spot and trigger tuned to illuminate a small area			
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Layer interconnection "super-ALPIDE"

- To study the bending and interconnection of large pieces of processed chips, "super-ALPIDE" is built
 - consists of 1 silicon piece cut from an ALPIDE wafer (9x2 dies, approx 1/2 of layer 0)



Layer interconnection (2) "super-ALPIDE"

- A bonding jig is being prepared
- the first row of ALPIDEs will be wire-bonded to an edge-FPC
 - just like the final detector.
- super-ALPIDE/L0 will be held by an exoskeleton that:
 - mimics L1
 - and allows to interconnect all remaining ALPIDE dies





long wires for testing



edge bonds (like final ITS3)



Key R&D for combining electrical and mechanical prototypes



Summary

- wafer-scale, 20-40 µm-thin, bent MAPS
- R&D on bent MAPS:
 - started with existing, thin MAPS within **ALICE ITS3**
 - in-beam verification of bent MAPS: successful
 - full-size mechanical mockups: build and characterised
- R&D on 65 nm MAPS:
 - joint effort within CERN EP R&D of several groups with large contribution from the ALICE **ITS3** community
 - first submission ("MLR1") came back: >50 prototype chips - detection efficiency of a 32x32 pixel prototype ("DPTS"): **100%**
- for several future vertex detectors

ALICE proposes to build the next-generation Inner Tracking System, based on 300 mm-

These newly developed detector technologies have a the potential to be a game changer

